

NTE553 Schottky Barrier Diode

Description:

The NTE553 is a silicon schottky barrier diode in a DO35 style package for use in UHF and VHF switching applications.

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Reverse Voltage, V_R	-35V
Forward Current, I_F	100mA
Power Dissipation, P_D	150mW
Operating Temperature Range, T_{opr}	-20° to $+60^\circ\text{C}$
Storage Temperature range, T_{stg}	-45° to $+125^\circ\text{C}$

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R = -10\mu\text{A}$	-35	-	-	V
Reverse Leakage Current	I_R	$V_R = -25\text{V}$	-	-	-0.1	μA
Forward Voltage	V_F	$I_F = 10\text{mA}$	-	-	1.0	V
Diode Capacitance	C_T	$V_R = -6\text{V}, f = 1\text{MHz}$	-	-	1.2	pf
Series Resistance	R_S	$I_F = 2\text{mA}, f = 100\text{MHz}$	-	-	1.2	Ω
Series Inductance	L_S	$f = 250\text{MHz}$	-	3	-	nH

